Akihiko Ohi

List of Publications by Year in descending order

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713013 932766 23 440 10 21 citations h-index g-index papers 23 23 23 668 all docs docs citations times ranked citing authors

#	Article	IF	CITATIONS
1	Interface characteristics of \hat{l}^2 -Ga2O3/Al2O3/Pt capacitors after postmetallization annealing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	7
2	Influence of HfO2 and SiO2 interfacial layers on the characteristics of n-GaN/HfSiO <i>x</i> capacitors using plasma-enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	2
3	Nanoantenna Structure with Mid-Infrared Plasmonic Niobium-Doped Titanium Oxide. Micromachines, 2020, 11, 23.	1.4	5
4	Correlation between SiO2 growth rate and difference in electronegativity of metal–oxide underlayers for plasma enhanced atomic layer deposition using tris(dimethylamino)silane precursor. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	6
5	A MEMS-Based Quad-Wavelength Hybrid Plasmonic–Pyroelectric Infrared Detector. Micromachines, 2019, 10, 413.	1.4	16
6	MEMS-Based Wavelength-Selective Bolometers. Micromachines, 2019, 10, 416.	1.4	19
7	Change of characteristics of n-GaN MOS capacitors with Hf-rich HfSiOx gate dielectrics by post-deposition annealing. Microelectronic Engineering, 2019, 216, 111036.	1.1	9
8	An Onâ€Chip Quadâ€Wavelength Pyroelectric Sensor for Spectroscopic Infrared Sensing. Advanced Science, 2019, 6, 1900579.	5.6	31
9	Investigation of Al2O3/GaN interface properties by sub-bandgap photo-assisted capacitance-voltage technique. AIP Advances, 2019, 9, .	0.6	17
10	Hafnium silicate gate dielectrics in GaN metal oxide semiconductor capacitors. Applied Physics Express, 2019, 12, 011009.	1.1	28
11	Improved leakage current properties of ZrO2/(Ta/Nb)Ox-Al2O3/ZrO2 nanolaminate insulating stacks for dynamic random access memory capacitors. Thin Solid Films, 2018, 655, 48-53.	0.8	16
12	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 061206.	0.6	5
13	Organic π-type thermoelectric module supported by photolithographic mold: a working hypothesis of sticky thermoelectric materials. Science and Technology of Advanced Materials, 2018, 19, 517-525.	2.8	27
14	Electron microscopy and ultraviolet photoemission spectroscopy studies of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2018, 57, 098003.	0.8	8
15	Influence of Oxidant Gas of Atomic Layer Deposition on Electrical Characteristics of Al ₂ 0 ₃ films. Vacuum and Surface Science, 2018, 61, 280-285.	0.0	5
16	Improvement of smooth surface of RuO2 bottom electrode on Al2O3 buffer layer and characteristics of RuO2/TiO2/Al2O3/TiO2/RuO2 capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	8
17	Low-energy ion scattering spectroscopy and reflection high-energy electron diffraction of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2017, 56, 128004.	0.8	16
18	Nanostructures Control the Hepatocellular Responses to a Cytotoxic Agent "Cisplatin― BioMed Research International, 2015, 2015, 1-10.	0.9	7

Акініко Оні

#	Article	IF	CITATIONS
19	Infrared Perfect Absorbers Fabricated by Colloidal Mask Etching of Al–Al ₂ O ₃ –Al Trilayers. ACS Photonics, 2015, 2, 964-970.	3.2	172
20	Aluminum infrared plasmonic perfect absorbers fabricated by colloidal lithography. , 2015, , .		1
21	Role of the (Ta/Nb)Ox/Al2O3 interface on the flatband voltage shift for Al2O3/(Ta/Nb)Ox/Al2O3 multilayer charge trap capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	10
22	The Effect of Physical and Chemical Cues on Hepatocellular Function and Morphology. International Journal of Molecular Sciences, 2014, 15, 4299-4317.	1.8	7
23	Electrical properties of anatase TiO2 films by atomic layer deposition and low annealing temperature. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	18